

L Number	Hits	Search Text	DB	Time stamp
31	586	(257/421-427).CCLS.	USPAT	2004/01/02 08:32
32	32	((257/421-427).CCLS.) and organic	USPAT; US-PGPUB; DERWENT	2004/01/02 08:35
33	13	(338/32r).CCLS.	US-PGPUB	2004/01/02 08:34
34	712	(338/32r).CCLS.	USPAT	2004/01/02 08:35
35	25	((338/32r).CCLS.) and organic	USPAT; US-PGPUB; DERWENT	2004/01/02 09:20
36	70	(324/200).CCLS.	USPAT	2004/01/02 09:20
-	149	substrate and insulat\$3 and magnetoresist\$4 and ((organic or polyimide or benzocyclobutene) with film) and shield\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 08:45
-	119	(substrate with insulat\$3) and magnetoresist\$4 and ((organic or polyimide or benzocyclobutene) with film) and shield\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/22 15:04
-	29	((organic or polyimide or benzocyclobutene) with film) same (reliev\$3 with stress)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 08:49
-	0	((organic or polyimide or benzocyclobutene) with film) and (reliev\$3 with stress) and (magnetoreisist\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/22 15:09
-	3	((organic or polyimide or benzocyclobutene) with film) and (reliev\$3 with stress) and (magnetoresist\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/28 08:36
-	3351	((Magnetic adj tunnel adj junction) or (MTJ) or TMR)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 08:19
-	767	((((Magnetic adj tunnel adj junction) or (MTJ) or TMR)) and substrate and insulat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 08:19
-	312	(((((Magnetic adj tunnel adj junction) or (MTJ) or TMR)) and substrate and insulat\$3) and shield\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 08:20
-	75	(((((Magnetic adj tunnel adj junction) or (MTJ) or TMR)) and substrate and insulat\$3) and shield\$3) and (organic or polyamide or (resist adj film) or benzocyclobutene)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 08:27
-	132	shield\$3 with cover\$3 with ((magneto adj resist\$4) or magnetorsist\$4 or MR or GMR or TMR or (magnetic adj tunnel adj junctionN))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 08:35
-	7	((("5062381") or ("1096815")).PN.	USPAT; US-PGPUB; DERWENT	2003/05/27 08:38
-	0	((("5062381") or ("1096815")).PN.	JPO	2003/05/27 08:48

-	167	((organic or polyimide or benzocyclobutene)) same (reliev\$3 with stress)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 08:49
-	2	((((organic or polyimide or benzocyclobutene)) same (reliev\$3 with stress) ) and ((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction)))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 08:51
-	60491	((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 09:09
-	101	((((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction))) and (shield\$3 same (organic or benzocyclobutane or (resist adj film) or polyimide) same insulat\$3))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/28 12:03
-	48	((((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction))) and (shield\$3 with (organic or benzocyclobutane or (resist adj film) or polyimide) same insulat\$3))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 08:57
-	45	((((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction))) and (shield\$3 with (organic or benzocyclobutane or (resist adj film) or polyimide) with insulat\$3))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 09:09
-	48843	denso.as.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 09:09
-	826	denso.as. and (shield\$3)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 09:09
-	0	(denso.as. and (shield\$3)) and ((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/28 08:25
-	0	(denso\$.as. and ((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction))) and shield\$3	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 09:11
-	27	(denso\$.as. and ((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction))) and insulat\$3	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/12/12 09:00
-	0	(denso\$.as. and ((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction))) and organic	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 09:12
-	1	(denso\$.as. and ((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction))) and polyimide	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 09:12
-	112	denso\$.as. and ((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 09:19
-	5	((("5806172") or ("5790353") or ("5471084") or ("6452381") or ("5618738"))).PN.	USPAT	2003/05/27 09:23
-	1	("20030094944").PN.	USPAT;	2003/05/27 09:23
-	2520	((324/252,249,207.21) or (438/48,51,99) or (360/319,320,324.2) or (428/692,694sl)).CCLS.	US-PGPUB USPAT	2003/05/27 10:26

-	458	((((324/252,249,207.21) or (438/48,51,99) or (360/319,320,324.2) or (428/692,694sl)).CCLS.) and ((organic with film) or polyimide or benzocyclobutane or (resist adj film)))	USPAT; US-PGPUB; DERWENT	2003/05/27 10:27
-	96	(((((324/252,249,207.21) or (438/48,51,99) or (360/319,320,324.2) or (428/692,694sl)).CCLS.) and ((organic with film) or polyimide or benzocyclobutane or (resist adj film))) and (shield\$3))	USPAT; US-PGPUB; DERWENT	2003/05/27 10:27
-	33	(((((324/252,249,207.21) or (438/48,51,99) or (360/319,320,324.2) or (428/692,694sl)).CCLS.) and ((organic with film) or polyimide or benzocyclobutane or (resist adj film))) and (shield\$3)) and (insulat\$3 with substrate)	USPAT; US-PGPUB; DERWENT	2003/05/27 10:27
-	25	(nippondenso\$.as. and ((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction))) and insulat\$3	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/28 09:06
-	3	(nippondenso\$.as. and (shield\$3)) and ((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/28 08:26
-	3	(nippondenso\$.as. and (shield\$3)) and ((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/28 08:26
-	206	(nippondenso\$.as. and ((organic with film) or polyimide or (resist adj film) or benzocyclobutane))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/28 08:35
-	9	((nippondenso\$.as. and ((organic with film) or polyimide or (resist adj film) or benzocyclobutane)) ) and (shield\$3)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/28 08:29
-	2	((nippondenso\$.as. and ((organic with film) or polyimide or (resist adj film) or benzocyclobutane)) ) and (reliev\$3 with thermal with stress\$3)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/28 08:35
-	102	((((organic with film) or polymide or (resist adj film) or benzocyclobutene) with film) and (reliev\$3 with thermal with stress))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/28 09:01
-	12	((magneto adj resist\$4) or MR or GMR or TMR or (magnetic adj tunnel adj junction) or magnetorsist\$4) and (reliev\$3 with thermal with stress)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/28 09:03
-	52	((nippondenso\$.as. or denso\$.as.) and ((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction))) and insulat\$3	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/28 09:07
-	246	((nippondenso\$.as. or denso\$.as.) and ((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction)))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/28 09:08
-	3	((nippondenso\$.as. or denso\$.as.) and ((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction))) and (shield\$3)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/28 09:07
-	6881	((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction)) and shield\$3	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/28 09:09

-	3403	((((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction)) and shield\$3) and insulat\$3	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/28 09:09
-	9962	"29" and (aluminum with wir\$3)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/28 09:10
-	41	((((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction)) and shield\$3) and insulat\$3) and (aluminum with wir\$3)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/28 09:12
-	0	36/324.2.ccls. and shield\$3	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/28 09:12
-	62	360/324.2.ccls. and shield\$3	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/28 09:17
-	0	360/324.2.ccls. and (reliev\$3 with stress)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/28 09:17
-	41	nickel with iron with "69"	USPAT; EPO; JPO; DERWENT	2003/05/28 11:39
-	144	nickel with iron with insulat\$3 with film	USPAT; EPO; JPO; DERWENT	2003/05/28 11:43
-	174	nickel with iron with shield\$3 with layer	USPAT; EPO; JPO; DERWENT	2003/05/28 14:39
-	45	nickel with iron with shield\$3 with layer	US-PGPUB	2003/05/28 12:02
-	210	nippondenso.as. or denso.as.	US-PGPUB	2003/05/28 12:02
-	0	(nippondenso.as. or denso.as.) and(((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction)))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/28 12:03
-	0	(nippondenso.as. or denso.as.) and (((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction)))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/05/28 12:03
-	2	(nippondenso.as. or denso.as.) and (((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction)))	US-PGPUB	2003/05/28 12:04
-	7669	((((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction)))	US-PGPUB	2003/05/28 12:04
-	902	(TMR or (magnetic adj tunnel adj junction))	US-PGPUB	2003/05/28 12:04
-	265	((TMR or (magnetic adj tunnel adj junction))) and shield\$3	US-PGPUB	2003/05/28 12:04
-	20	((TMR or (magnetic adj tunnel adj junction))) and shield\$3) and serial\$2	US-PGPUB	2003/05/28 12:11
-	1	("54127363").PN.	USPAT; US-PGPUB; JPO; DERWENT	2003/05/28 14:23
-	11	nickel with iron with shield\$3 with "%"	USPAT	2003/05/28 14:41
-	8	(nickel with "%") same shield same iron	USPAT	2003/05/28 14:42
-	24	(nickel with "%") same shield\$3 same iron	USPAT	2003/05/28 14:44
-	64	((nickel or Ni) with "%") same shield\$3 same (iron or Fe)	USPAT	2003/05/28 14:45
-	0	shield with layer with undercut with wall	USPAT	2003/05/28 15:10
-	7	shield with layer with undercut	USPAT	2003/05/28 15:11
-	99	shield with undercut	USPAT	2003/05/28 15:11
-	149669	(360/324\$).CCLS. or ("428").CLAS.	USPAT; US-PGPUB	2003/12/04 15:14

-	149925	(360/324-327.33).CCLS. or ("428").CLAS.	USPAT; US-PGPUB	2003/12/04 15:14
-	909	((360/324-327.33).CCLS. or ("428").CLAS.) and (organic adj film)	USPAT; US-PGPUB;	2003/12/04 15:14
-	778	((360/324-327.33).CCLS. or ("428").CLAS.) and (organic adj film)) and substrate	DERWENT USPAT; US-PGPUB;	2003/12/04 15:14
-	48	((360/324-327.33).CCLS. or ("428").CLAS.) and (organic adj film)) and substrate) and shield	DERWENT USPAT; US-PGPUB;	2003/12/04 15:18
-	51	((360/324-327.33).CCLS. or ("428").CLAS.) and (organic adj film)) and shield	DERWENT USPAT; US-PGPUB;	2003/12/04 15:20
-	31	(organic adj film) with shield	DERWENT USPAT; US-PGPUB;	2003/12/04 15:20
-	2	(organic adj film) same shield same (tunnel adj junction)	DERWENT USPAT; US-PGPUB;	2003/12/04 15:21
-	2	(organic adj film) same shield and (tunnel adj junction)	DERWENT USPAT; US-PGPUB;	2003/12/04 15:21
-	9	(organic adj film) and (tunnel adj junction)	DERWENT USPAT; US-PGPUB;	2003/12/04 15:23
-	16	(thermal\$2 adj stress\$3) and (tunnel adj junction)	DERWENT USPAT; US-PGPUB;	2003/12/04 15:26
-	119	(360/324.2).CCLS.	DERWENT USPAT	2003/12/04 15:55
-	9993	organic adj film	USPAT; US-PGPUB;	2003/12/12 08:52
-	29	(organic adj film) same (thermal\$3 with stress\$3)	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2003/12/12 08:53
-	44	(organic adj film) same ((thermal\$3 or heat\$3) with stress\$3)	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2003/12/12 08:53
-	28	(denso\$.as. and ((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction))) and insulat\$3	EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/12/31 09:02
-	42	murata-yuichiro.in.	EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/12/31 09:00
-	46	toyoda-inao.in.	EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/12/31 08:58
-	291	suzuki-yasutoshi.in.	EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/12/12 09:30
-	223	suzuki-yasutoshi.in. and (denso or nippondenso).as.	EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/12/12 09:36

-	25	(suzuki-yasutoshi.in. and (denso or nippondenso).as.) and shield\$3	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 08:57
-	55	((magnetoresistive) with serial\$2)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/12/12 09:47
-	244	((magnetoresistive or mr) with serial\$2)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/12/12 09:48
-	0	((((magnetoresistive or mr) with serial\$2)) and (organic near3 film)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/12/12 09:48
-	1	((((magnetoresistive or mr) with serial\$2)) and (organic with film)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/12/12 09:48
-	16	((((magnetoresistive or mr) with serial\$2)) and shield	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/12/12 10:01
-	1309	(428/692,693,694tp).CCLS.	USPAT; US-PGPUB	2003/12/12 10:02
-	8	((428/692,693,694tp).CCLS.) and (substrate with insulat\$3 with silicon)	USPAT; US-PGPUB; DERWENT	2003/12/12 10:05
-	21	((428/692,693,694tp).CCLS.) and (substrate same insulat\$3 same silicon)	USPAT; US-PGPUB; DERWENT	2003/12/12 10:08
-	2	((428/692,693,694tp).CCLS.) and (serial\$2 with (magnetoresist\$4 or mr or (magneto adj resist\$4)))	USPAT; US-PGPUB; DERWENT	2003/12/12 10:09
-	386	(serial\$2 with (magnetoresist\$4 or mr or (magneto adj resist\$4)))	USPAT; US-PGPUB; DERWENT	2003/12/12 10:13
-	164	((serial\$2 with (magnetoresist\$4 or mr or (magneto adj resist\$4)))) and sensor	USPAT; US-PGPUB; DERWENT	2003/12/12 10:09
-	295	((serial\$2 with (magnetoresist\$4 or mr or (magneto adj resist\$4)))) not (serial with no\$2)	USPAT; US-PGPUB; DERWENT	2003/12/12 10:11
-	107	(serial\$2 with connect\$3 with (magnetoresist\$4 or mr or (magneto adj resist\$4)))	USPAT; US-PGPUB; DERWENT	2003/12/12 10:14
-	12	((serial\$2 with connect\$3 with (magnetoresist\$4 or mr or (magneto adj resist\$4)))) and shield\$3	USPAT; US-PGPUB; DERWENT	2003/12/12 10:14
-	820	substrate same magnetoresist\$4 same shield\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 08:46
-	54	(substrate same magnetoresist\$4 same shield\$3) and (shield with top with magnetoresist\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 08:49
-	69	(substrate same magnetoresist\$4 same shield\$3) and (shield with two with magnetoresist\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 08:49

-	25	(suzuki-yasutoshi.in. and (denso or nippondenso).as.) and shield\$3	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 13:32
-	46	toyoda-inao.in.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 08:59
-	42	murata-yuichiro.in.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 09:00
-	29	(denso\$.as. and ((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction))) and insulat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 09:03
-	54	((denso\$.as. or nippondenso.as.) and ((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction))) and insulat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 09:06
-	0	((denso\$.as. or nippondenso.as.) and ((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction))) and (substrate with shield\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 09:06
-	71	((denso\$.as. or nippondenso.as.) and ((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction))) and (substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 09:09
-	494	((magneto adj resist\$4) or magnetoresist\$4 or mr or gmr or TMR or (magnetic adj tunnel adj junction)) with substrate with two)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 10:08
-	0	("0903591").PN.	EPO; DERWENT	2003/12/31 10:08
-	4	pant.in. and shield\$3	USPAT; US-PGPUB; DERWENT	2003/12/31 10:23
-	4	pant-\$.in. and shield\$3	USPAT; US-PGPUB; DERWENT	2003/12/31 10:39
-	2	("6191577").PN.	USPAT; US-PGPUB; DERWENT	2003/12/31 13:16
-	0	("(thermaladjstress)withrelie\$4").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 13:16
-	0	("(thermaladjstress)withrelie\$4").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 13:17
-	1227	(thermal adj stress) with relie\$4	USPAT; US-PGPUB; DERWENT	2003/12/31 13:17
-	3	((thermal adj stress) with relie\$4) with film) same organic	USPAT; US-PGPUB; DERWENT	2003/12/31 13:18

-	52	((thermal adj stress) with relie\$4) with film	USPAT; US-PGPUB; DERWENT	2003/12/31 13:18
-	339	(passivation adj film) with organic	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 13:32
-	13	((passivation adj film) with organic) and (thermal adj stress)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/12/31 13:33